

Day : Tuesday
 Date: 4/26/2005

Time: 11:37:34

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = BENSAHEL

First Name = DANIEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>06042081</u>	<u>4263056</u>	150	05/24/1979	METHOD FOR THE MANUFACTURE OF LIGHT EMITTING AND/OR PHOTODETECTIVE DIODES	BENSAHEL, DANIEL
<u>06085948</u>	<u>4229237</u>	150	10/18/1979	METHOD OF FABRICATION OF SEMICONDUCTOR COMPONENTS HAVING OPTOELECTRONIC CONVERSION PROPERTIES	BENSAHEL, DANIEL
<u>06853906</u>	<u>4678538</u>	250	04/21/1986	PROCESS FOR THE PRODUCTION OF AN INSULATING SUPPORT ON AN ORIENTED MONOCRYSTALLINE SILICON FILM WITH LOCALIZED DEFECTS	BENSAHEL, DANIEL
<u>06882901</u>	<u>4725561</u>	150	06/05/1986	PROCESS FOR THE PRODUCTION OF MUTUALLY ELECTRICALLY INSULATED MONOCRYSTALLINE SILICON ISLANDS USING LASER RECRYSTALLIZATION	BENSAHEL, DANIEL
<u>07808745</u>	<u>5252181</u>	150	12/17/1991	METHOD FOR CLEANING THE SURFACE OF A SUBSTRATE WITH PLASMA	BENSAHEL, DANIEL
<u>07914380</u>	Not Issued	161	07/15/1992	DEVICE FOR INJECTING A PRODUCT INTO AN ENCLOSED CHAMBER SUCH AS A REACTOR FOR MICROELECTRONICS	BENSAHEL, DANIEL
<u>08797511</u>	<u>5876796</u>	150	12/23/1996	PROCESS FOR SELECTIVELY DEPOSITING A REFRACTORY METAL SILICIDE ON SILICON, AND SILICON WAFER	BENSAHEL, DANIEL

				METALLIZED USING THIS PROCESS	
<u>09217025</u>	6117750	150	12/21/1998	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY	BENSAHEL, DANIEL
<u>09403356</u>	6372581	150	10/18/1999	PROCESS FOR NITRIDING THE GATE OXIDE LAYER OF A SEMICONDUCTOR DEVICE AND DEVICE OBTAINED	BENSAHEL, DANIEL
<u>09403442</u>	6255149	150	10/19/1999	PROCESS FOR RESTRICTING INTERDIFFUSION IN A SEMICONDUCTOR DEVICE WITH COMPOSITE SI/SIGE GATE	BENSAHEL, DANIEL
<u>09540188</u>	6399502	150	03/31/2000	PROCESS FOR FABRICATING A PLANAR HETEROSTRUCTURE	BENSAHEL, DANIEL
<u>09659913</u>	6429098	150	09/11/2000	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM OR SILICON ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON OR GERMANIUM, RESPECTIVELY, AND MULTILAYER PRODUCTS OBTAINED	BENSAHEL, DANIEL
<u>09763532</u>	6551698	150	04/04/2001	METHOD FOR TREATING A SILICON SUBSTRATE, BY NITRIDING, TO FORM A THIN INSULATING LAYER	BENSAHEL, DANIEL
<u>09786996</u>	6537370	150	03/09/2001	PROCESS FOR OBTAINING A LAYER OF SINGLE-CRYSTAL GERMANIUM ON A SUBSTRATE OF SINGLE-CRYSTAL SILICON, AND PRODUCTS OBTAINED	BENSAHEL, DANIEL
<u>09921642</u>	6596555	150	08/03/2001	FORMING OF QUANTUM DOTS	BENSAHEL, DANIEL
<u>10048719</u>	6690027	150	06/13/2002	METHOD FOR MAKING A DEVICE COMPRISING LAYERS OF PLANES OF QUANTUM DOTS	BENSAHEL, DANIEL
<u>10405075</u>	Not	061	03/31/2003	STRAINED-CHANNEL	BENSAHEL,

	Issued			ISOLATED-GATE FIELD EFFECT TRANSISTOR, PROCESS FOR MAKING SAME AND RESULTING INTEGRATED CIRCUIT	DANIEL
<u>10614675</u>	Not Issued	071	07/07/2003	GROWTH OF A SINGLE-CRYSTAL REGION OF A III-V COMPOUND ON A SINGLE-CRYSTAL SILICON SUBSTRATE	BENSAHEL, DANIEL
<u>10615259</u>	Not Issued	090	07/09/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
<u>10744680</u>	Not Issued	051	12/23/2003	METHOD FOR FORMING A LOCALIZED REGION OF A MATERIAL DIFFICULT TO ETCH	BENSAHEL, DANIEL
<u>10815473</u>	Not Issued	030	04/01/2004	METHOD OF FABRICATING A SEMICONDUCTOR DEVICE COMPRISING A GATE DIELECTRIC MADE OF HIGH DIELECTRIC PERMITTIVITY MATERIAL	BENSAHEL, DANIEL
<u>10816214</u>	Not Issued	030	04/01/2004	HETEROATOMIC SINGLE-CRYSTAL LAYERS	BENSAHEL, DANIEL
<u>10882995</u>	Not Issued	030	07/01/2004	PROCESS FOR FABRICATING STRAINED LAYERS OF SILICON OR OF A SILICON/GERMANIUM ALLOY	BENSAHEL, DANIEL
<u>60445825</u>	Not Issued	159	02/10/2003	PROCESS FOR TRANSFERRING A LAYER OF STRAINED SEMICONDUCTOR MATERIAL	BENSAHEL, DANIEL
<u>60461656</u>	Not Issued	159	04/09/2003	TERAHERTZ SOURCES AND DETECTORS BASED ON SILICON AND SILICON GERMANIUM ALLOYS AND METHOD OF MANUFACTURE	BENSAHEL, DANIEL

Inventor Search Completed: No Records to Display.

Search Another: Inventor	Last Name <input type="text" value="Bensahel"/>	First Name <input type="text" value="Daniel"/>	<input type="button" value="Search"/>
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Examiner's Notes

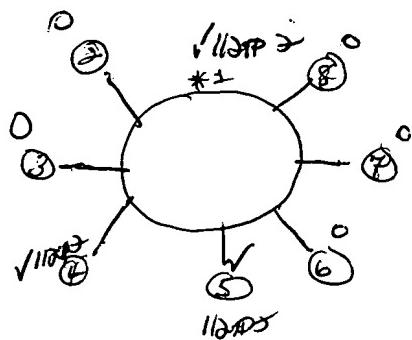
James H. Morris
Tel (617) 730-3500

Sep 16 1975

117184, 89, 101

Written Restriction Requested on 1/4/05

- s (single(a) crystal? or monocrystal?) (6a) (wafer or substrate?)
s (III(w)IV) (4a) (compound d#)
s (single(w) crystal?) (8a) (region or area)
s (Ge or germanium (4a) layer) (10a) (single(w) crystal? or mono(w) crystal?)
s (etch?) (8a) (germanium (4a) layer or Ge (4a) layer)
s (crys tallographic(w) plane)



112PP2 Rej
Claim 1, lines 5-6, "... bottom... (No antecedence)

Claim 4, line 2, "... germanium allow..." (No antecedence)

Claim 5, line 3, "... shape of..." (No antecedence)